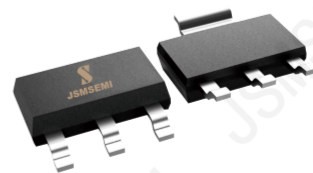


FEATURES

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complementary types: BCP51 ... BCP53 (PNP)



SOT-223

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	BCP54	BCP55	BCP56	Unit
V _{CBO}	Collector-Base Voltage	45	60	100	V
V _{CEO}	Collector-Emitter Voltage	45	60	80	V
V _{EBO}	Emitter-Base Voltage	5			V
I _C	Collector Current -Continuous	1			A
P _C	Collector Power Dissipation	1.5			W
R _{θJA}	Thermal Resistance Junction to Ambient	83.3			°C/W
T _{stg}	Storage Temperature Range	-65~+150			°C

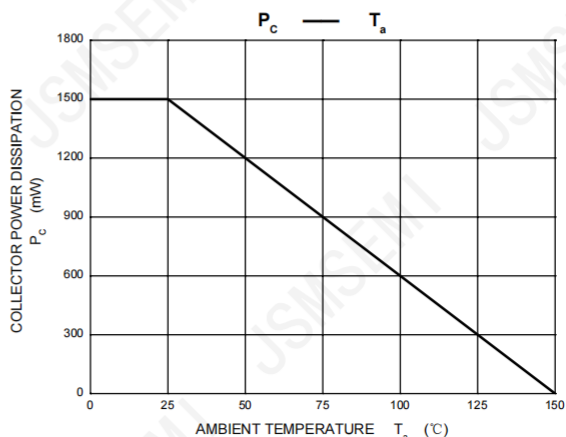
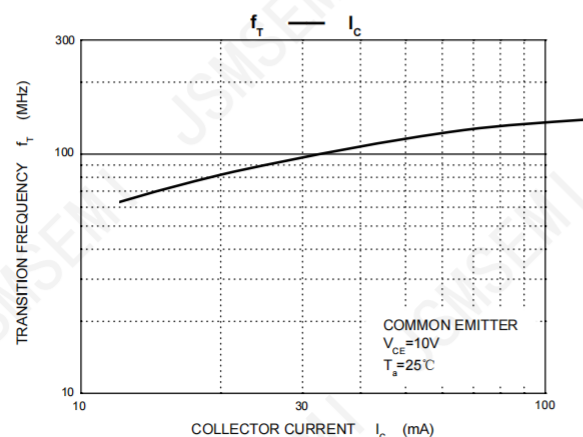
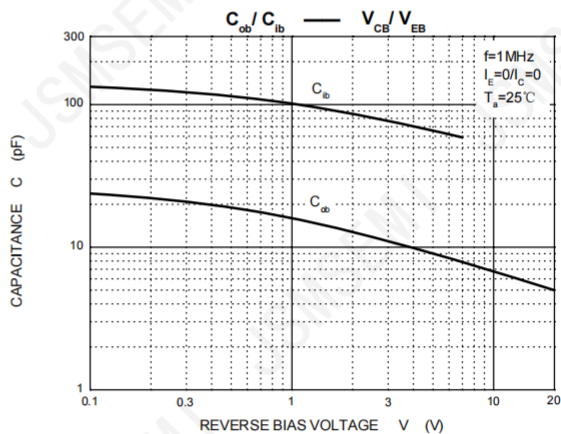
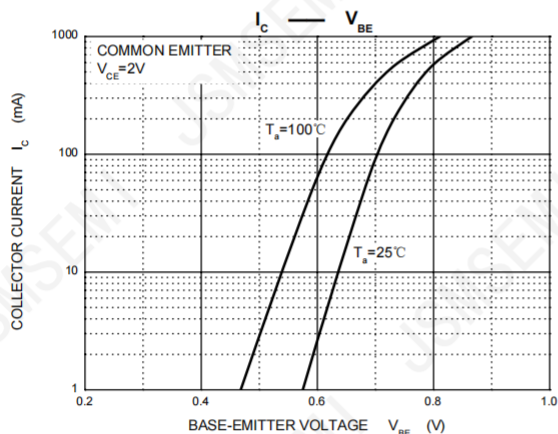
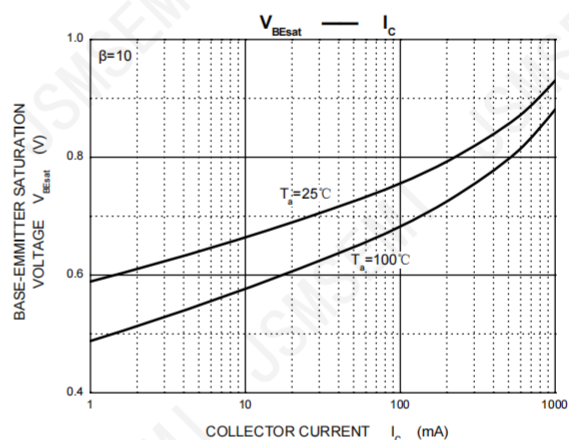
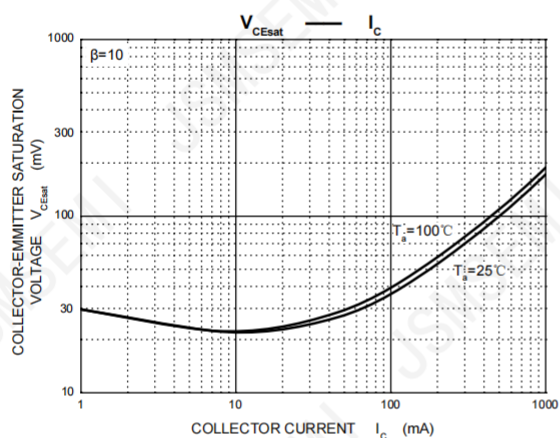
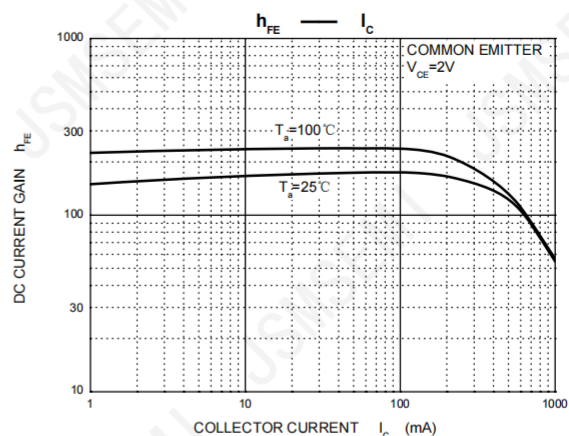
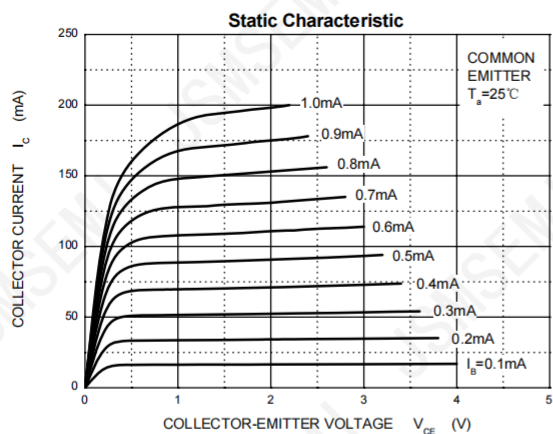
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 0.1mA, I _E =0	45		V
			60		
			100		
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10mA, I _B =0	45		V
			60		
			80		
Base-emitter breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C =0	5		V
Collector cut-off current	I _{CBO}	V _{CB} = 30 V, I _E =0		100	nA
DC current gain	h _{FE(1)}	V _{CE} = 2V, I _C =5mA	25		
	h _{FE(2)}	V _{CE} = 2V, I _C =150m A	63	250	
	h _{FE(3)}	V _{CE} = 2V, I _C =500m A	25		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500mA, I _B =50mA		0.5	V
Base-emitter voltage	V _{BE}	V _{CE} =2V, I _C =500m A		1	V
Transition frequency	f _T	V _{CE} =10V, I _C =50mA, f=100MHz	100		MHz

CLASSIFICATION OF h_{FE(2)}

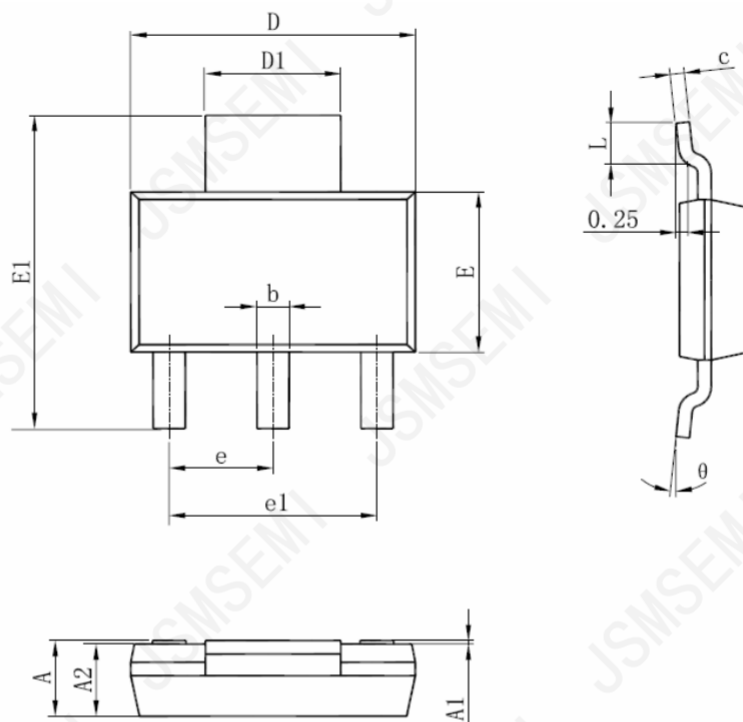
Rank	BCP54-10,115, BCP55-10,115, BCP56-10,115	BCP54-16,115, BCP55-16,115, BCP56-16,115
Range	63-160	100-250

Typical Characteristics



Package Information

SOT-223



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.520	1.800	0.060	0.071
A1	0.000	0.100	0.000	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.820	0.026	0.032
c	0.250	0.350	0.010	0.014
D	6.200	6.400	0.244	0.252
D1	2.900	3.100	0.114	0.122
E	3.300	3.700	0.130	0.146
E1	6.830	7.070	0.269	0.278
e	2.300(BSC)		0.091(BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.150	0.035	0.045
θ	0°	10°	0°	10°

Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

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